

**IN THE CLAIMS**

1. (Currently Amended) A semiconductor device, comprising:  
a plurality of metal line patterns having a predetermined surface area size, wherein two adjacent metal line patterns are spaced a predetermined distance less than 10  $\mu\text{m}$  apart from each other [at a predetermined distance].
2. (Original) A semiconductor device as claimed in claim 1, wherein the predetermined distance is greater than 1.0  $\mu\text{m}$ .
3. (Original) A semiconductor device as claimed in claim 1, wherein the predetermined distance is greater than 1.5  $\mu\text{m}$ .
4. (Original) A semiconductor device as claimed in claim 1, wherein the plurality of metal line patterns have a surface area size of greater than “ $30\mu\text{m} \times 30\mu\text{m}$ ”.
5. (Currently Amended) A semiconductor device, comprising:  
a metal line layer having a plurality of metal line patterns spaced less than 10  $\mu\text{m}$  apart from each other; and  
at least one underlying layer under the metal line layer,  
wherein the space between two adjacent metal line patterns has a sufficient width to prevent a crack from occurring in the underlying layer.
6. (Original) A semiconductor device as claimed in claim 5, wherein the width of the space is greater than 1.0  $\mu\text{m}$ .
7. (Original) A semiconductor device as claimed in claim 5, wherein the width of the space is greater than 1.5  $\mu\text{m}$ .
8. (Original) A semiconductor device as claimed in claim 5, wherein the underlying layer is an insulating layer.
9. (Original) A semiconductor device as claimed in claim 5, wherein the metal line pattern has a surface area size of greater than “ $30\mu\text{m} \times 30\mu\text{m}$ ”.

10. (Currently Amended) A semiconductor device, comprising:  
a plurality of metal line patterns, wherein two adjacent metal line patterns are spaced less than 10  $\mu\text{m}$  apart from each other, and at least one of the two adjacent metal line patterns has a slit.

11. (Original) A semiconductor device as claimed in claim 10, wherein the slit has a width of greater than 1.0  $\mu\text{m}$ .

12. (Original) A semiconductor device as claimed in claim 11, wherein the slit is formed at a predetermined distance from an edge of the metal line pattern.

13. (Original) A semiconductor device as claimed in claim 12, wherein the predetermined distance is less than 4  $\mu\text{m}$ .

14. (Currently Amended) A semiconductor device having a multi-layered structure, comprising:

a metal line layer having a plurality of metal line patterns spaced less than 10  $\mu\text{m}$  apart from each other;  
at least one underlying layer under the metal line layer; and  
a slit formed at a sufficient distance from a space between two adjacent metal line patterns to prevent a crack from occurring in the underlying layer.

15. (Original) A semiconductor device as claimed in claim 14, wherein the slit is formed in a direction parallel to the space between two adjacent metal line patterns.

16. (Original) A semiconductor device as claimed in claim 14, wherein the slit has a width greater than 1.0  $\mu\text{m}$ .

17. (Original) A semiconductor device as claimed in claim 14, wherein the distance from the space between the two adjacent metal line patterns to the slit is less than 4.0  $\mu\text{m}$ .

18. (Withdrawn) A method of manufacturing a semiconductor device having a multi-layered structure, comprising:

forming at least one underlying layer on a semiconductor substrate; and

forming a metal line layer on the underlying layer, the metal line layer having a plurality of metal line patterns spaced apart from each other at a predetermined distance.

19. (Withdrawn) A method as claimed in claim 18, wherein the predetermined distance is greater than 1.0  $\mu\text{m}$ .

20. (Withdrawn) A method as claimed in claim 18, wherein the predetermined distance is greater than 1.5  $\mu\text{m}$ .

21. (Withdrawn) A method of manufacturing a semiconductor device having a multi-layered structure, comprising:

forming at least one underlying layer on a substrate;

forming simultaneously a metal line layer on the underlying layer and a slit, the metal line layer having a plurality of metal line patterns spaced apart from each other, at least one of either of two adjacent metal lines has a slit.

22. (Withdrawn) A method as claimed in claim 21, wherein the slit is formed in a direction parallel to the space between two adjacent metal line patterns.

23. (Withdrawn) A method as claimed in claim 21, wherein a width of the slit is greater than 1.0  $\mu\text{m}$ .

24. (Withdrawn) A method as claimed in claim 21, wherein a distance from the space between two adjacent metal line patterns to the slit is less than 4.0  $\mu\text{m}$ .

25. (Withdrawn) A method of manufacturing a semiconductor device, comprising:

forming at least one underlying layer on a substrate;

forming simultaneously a metal line layer on the underlying layer and a slit, the metal line layer having a plurality of metal line patterns spaced apart from each other, the slit formed at a sufficient distance from a space between the two adjacent metal line patterns in order to prevent a crack from occurring in the underlying layer.

26. (Withdrawn) A method as claimed in claim 25, wherein the slit is formed in a direction parallel to the space between two adjacent metal line patterns.

27. (Withdrawn) A method as claimed in claim 25, wherein the width of the slit is greater than 1.0  $\mu\text{m}$ .

28. (Withdrawn) A method as claimed in claim 25, wherein the distance between the slit and the space between two adjacent metal line patterns is less than 4.0  $\mu\text{m}$ .

29. (New) A semiconductor device, comprising:  
a plurality of metal line patterns, wherein two adjacent metal line patterns are spaced less than 1.5  $\mu\text{m}$  apart from each other, and at least one of the two adjacent metal line patterns has a slit.

30. (New) A semiconductor device having a multi-layered structure, comprising:  
a metal line layer having a plurality of metal line patterns spaced apart from each other;  
at least one underlying layer under the metal line layer; and  
a slit formed less than 4  $\mu\text{m}$  from a space between two adjacent metal line patterns in order to prevent a crack from occurring in the underlying layer.